

SCHOTTKY BARRIER DIODES

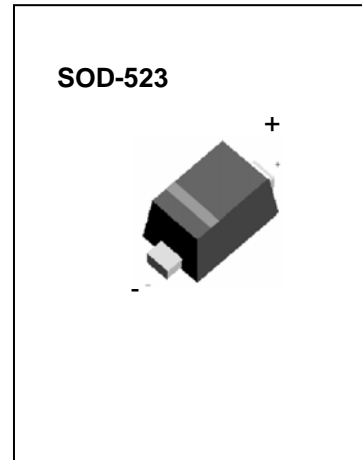
PRODUCT SUMMARY

SOD-523 Plastic-Encapsulate Diodes

FEATURES

Small surface mounting type
 Low I_R . ($I_R = 0.1 \mu A$)
 High reliability

 **Pb-free; RoHS-compliant**



MARKING: B

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Single Diode @ $T_A=25^\circ C$

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40-125	$^\circ C$

ELECTRICAL RATINGS @ $T_A=25^\circ C$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.6	V	$I_F=200mA$
Reverse current	I_R			1	μA	$V_R=10V$

TYPICAL CHARACTERISTICS

● Electrical characteristic curves (Ta=25°C)

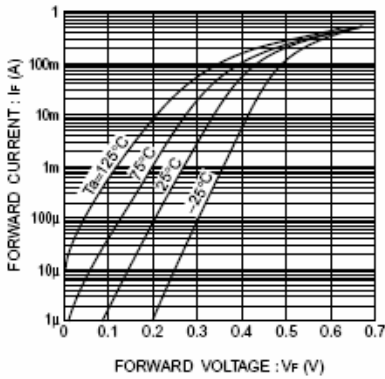


Fig. 1 Forward characteristics

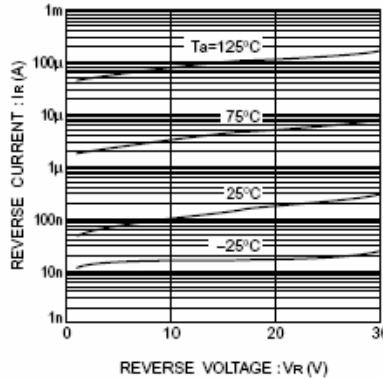


Fig. 2 Reverse characteristics

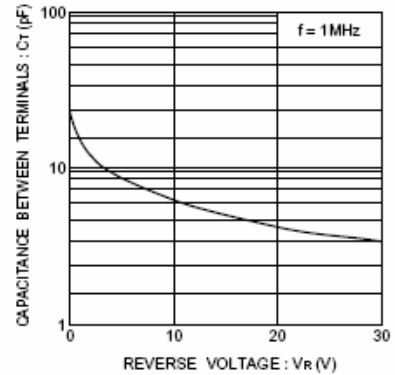


Fig. 3 Capacitance between terminals characteristics

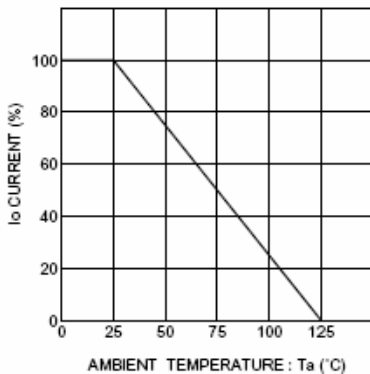


Fig 4. Derating curve
(mounting on glass epoxy PCBs)

Information furnished by Silicon Standard Corporation is believed to be accurate and reliable. However, Silicon Standard Corporation makes no guarantee or warranty, expressed or implied, as to the reliability, accuracy, timeliness or completeness of such information and assumes no responsibility for its use, or for infringement of any patent or other intellectual property rights of third parties that may result from its use. Silicon Standard reserves the right to make changes as it deems necessary to any products described herein for any reason, including without limitation enhancement in reliability, functionality or design. No license is granted, whether expressly or by implication, in relation to the use of any products described herein or to the use of any information provided herein, under any patent or other intellectual property rights of Silicon Standard Corporation or any third parties.